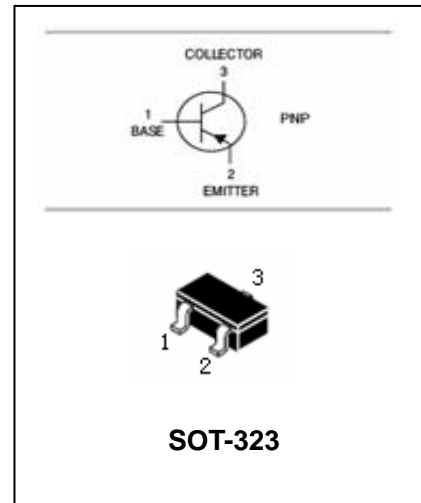


PNP Silicon Epitaxial Planar Transistor

BC807W

FEATURES

- High current(max.500mA)
- Low voltage.
- Complements the BC817W.



APPLICATIONS

- For general purpose amplification and switching.

ORDERING INFORMATION

Type No.	Marking	Package Code
BC807W	5A/5B/5C	SOT-323

MAXIMUM RATING @ Ta=25°C unless otherwise specified

Symbol	Parameter	Value	Units
V _{CBO}	Collector-Base Voltage	-50	V
V _{CEO}	Collector-Emitter Voltage	-45	V
V _{EBO}	Emitter-Base Voltage	-5	V
I _C	Collector Current -Continuous	-500	mA
P _C	Collector Dissipation	200	mW
T _j , T _{stg}	Junction and Storage Temperature	-65~150	°C

PNP Silicon Epitaxial Planar Transistor

BC807W

ELECTRICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -10\mu A, I_E = 0$	-50			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -2mA, I_B = 0$	-45			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -10\mu A, I_C = 0$	-5			V
Collector cut-off current	I_{CBO}	$V_{CB} = -20V, I_E = 0$			-0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = -5V, I_B = 0$			-0.1	μA
DC current gain	h_{FE}	$V_{CE} = -1V, I_C = -100mA$ BC807-16W BC807-25W BC807-40W	100 160 250		250 400 600	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -500mA, I_B = -50mA$			0.7	V
Transition frequency	f_T	$V_{CE} = -5V, I_C = -10mA$ $f = 100MHz$	80			MHz
Collector output capacitance	C_{ob}	$V_{CB} = -10V, I_E = 0, f = 1MHz$			10	pF

TYPICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified

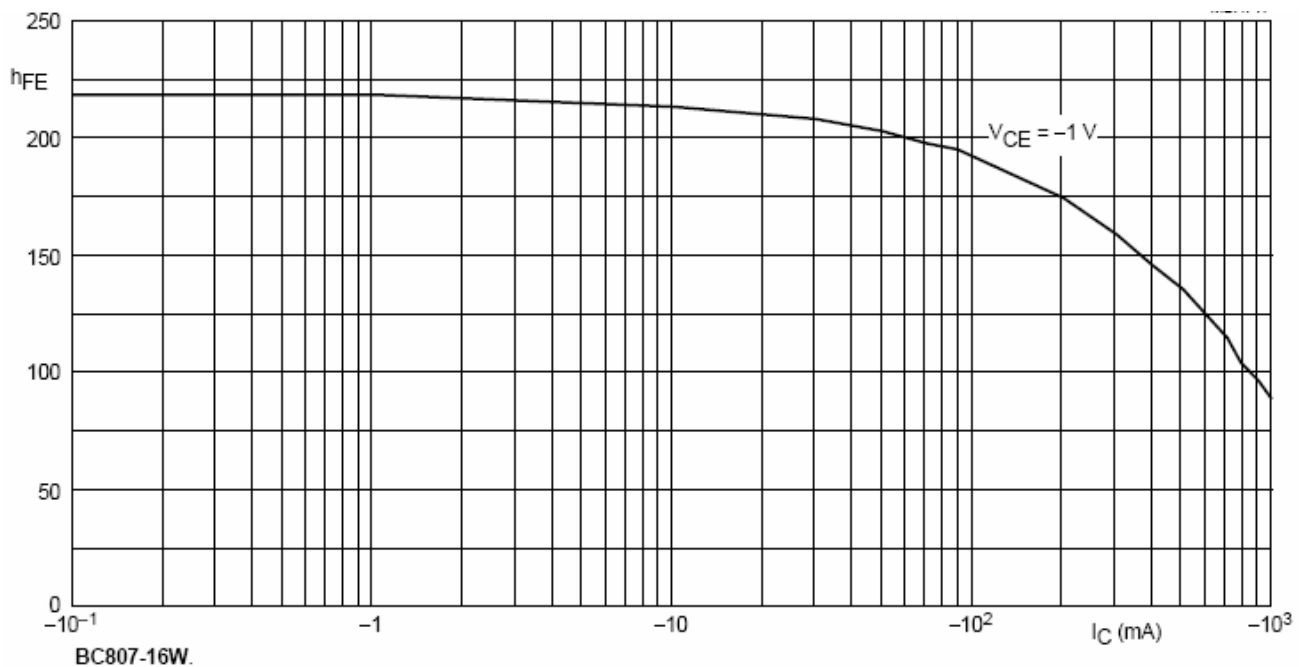
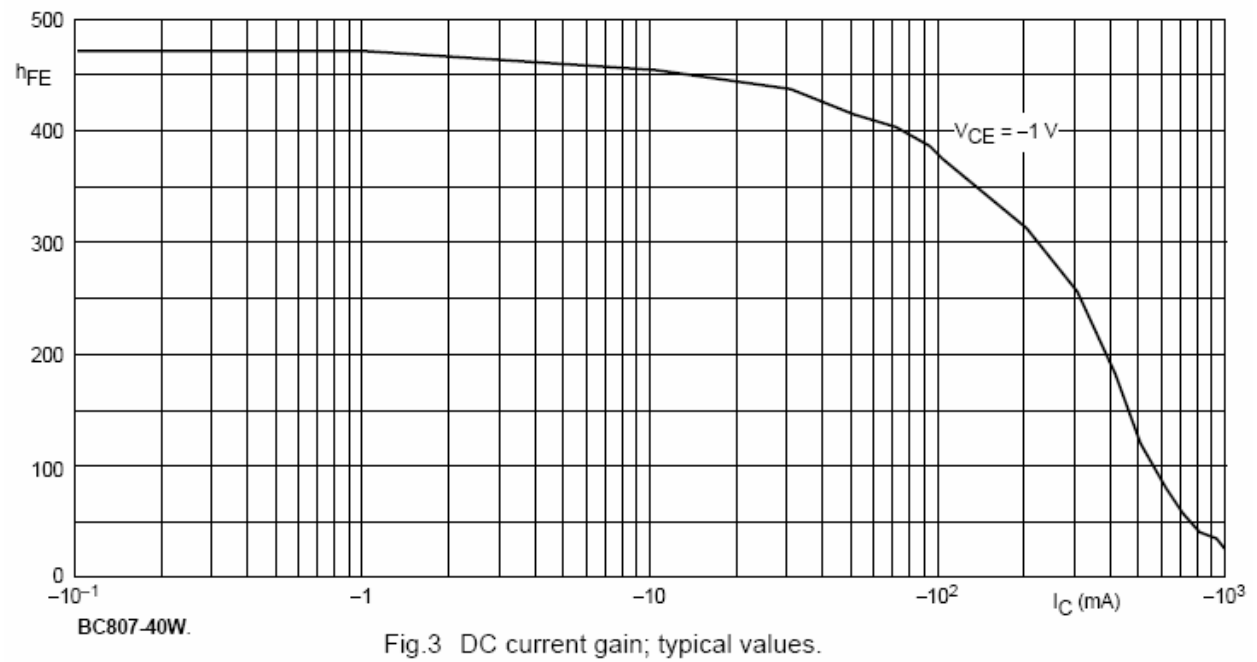
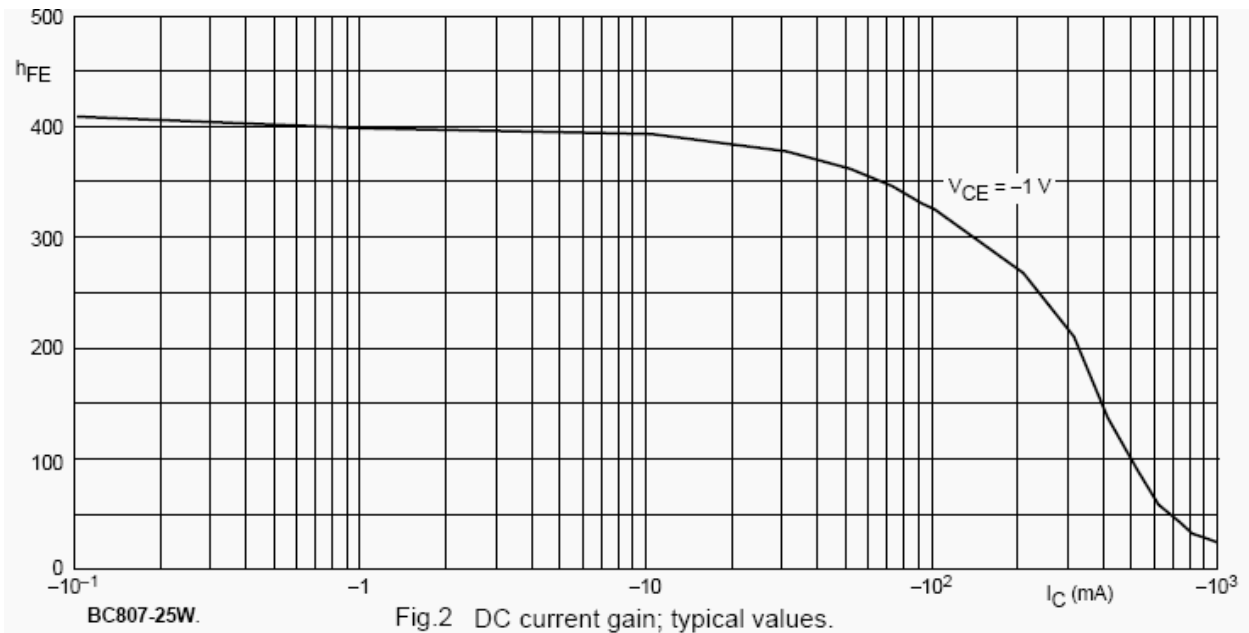


Fig.1 DC current gain; typical values.

PNP Silicon Epitaxial Planar Transistor

BC807W



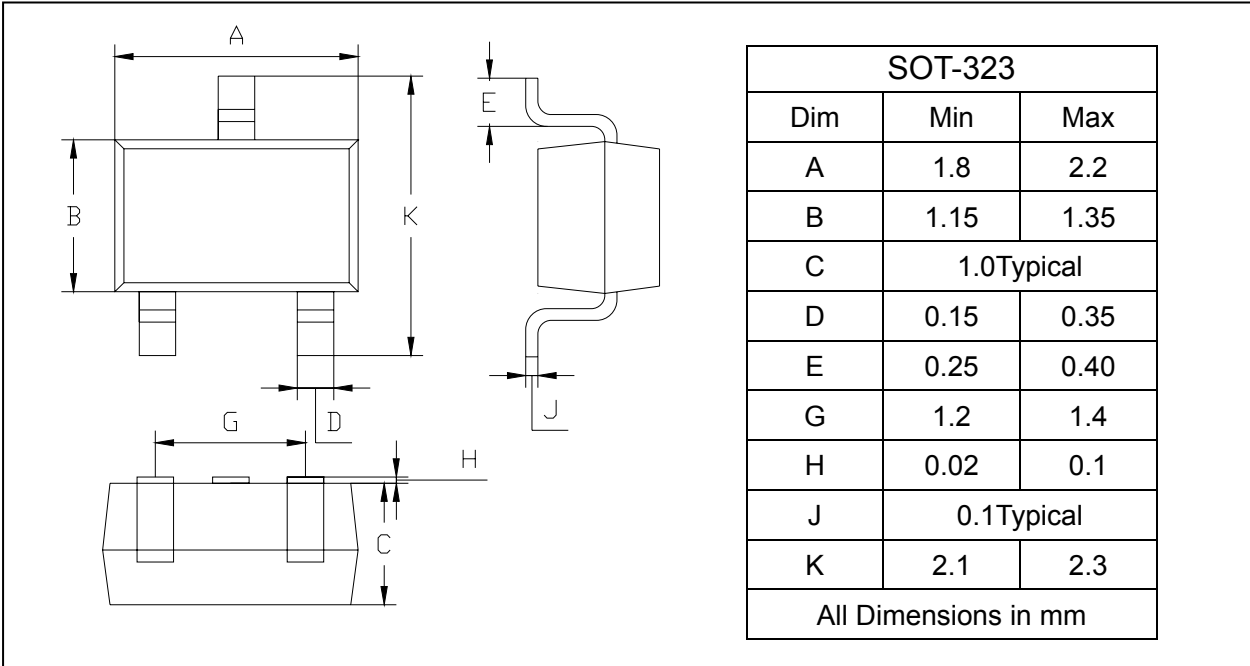
PNP Silicon Epitaxial Planar Transistor

BC807W

PACKAGE OUTLINE

Plastic surface mounted package

SOT-323



PACKAGE INFORMATION

Device	Package	Shipping
BC807W	SOT-323	3000/Tape&Reel